

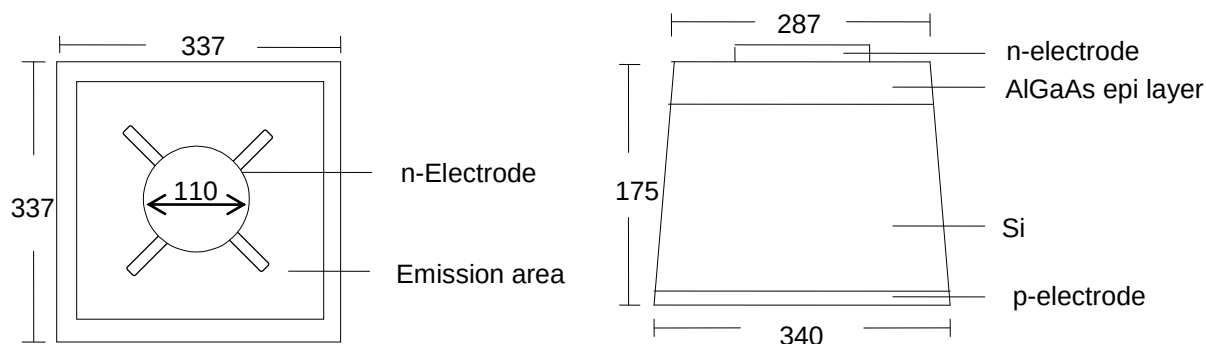
■ Features :

- Suitable for New Creative Products

■ Typical Applications :

- Home entertainment
- Light source for CMOS & CCD camera
- Security camera, CCTV

■ Outline Dimensions : (Unit: μm)



■ Physical Structure :

LED Chip dimension	Chip size	337 μm x 337 μm
	Thickness	175 $\pm$ 25 μm
	Emission area	287 $\pm$ 20 μm
	Bonding pad	110 μm
Electrode	Top: N (anode)	Gold
	Backside: P (cathode)	Gold
Surface condition	Frosted	

■ Electro-Optical Characteristics : ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward voltage	V_{FH}	$I_F = 100 \text{ mA}$	1.5	1.65	1.9	V
Reverse Voltage	I_R	$V_R = 10\text{V}$	-	-	5	μA
Radiant Power	P_o	$I_F = 100 \text{ mA}$	12	-	-	mW
Wavelength	λ_P	$I_F = 100 \text{ mA}$	-	855	-	nm
Spectral width at half height	$\Delta\lambda$	$I_F = 100 \text{ mA}$	-	30	-	nm

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

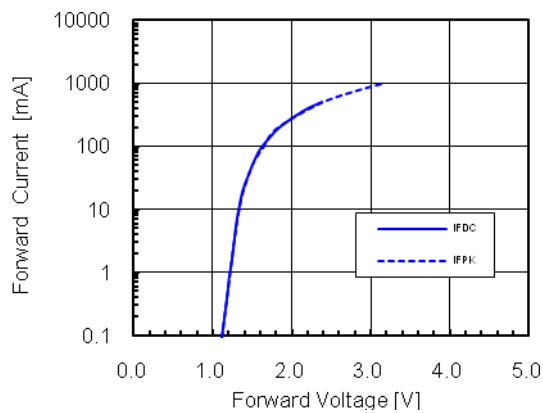


Fig 2. Relative Radiant Power vs. Wavelength

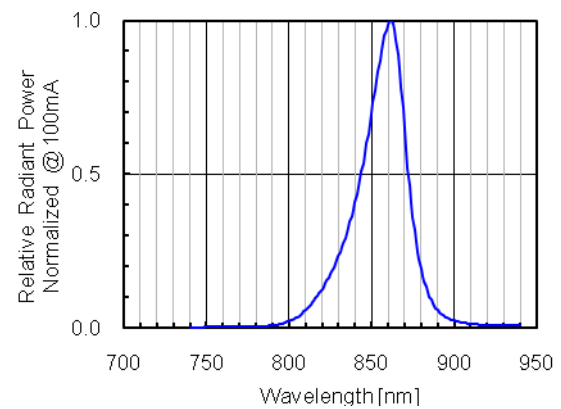
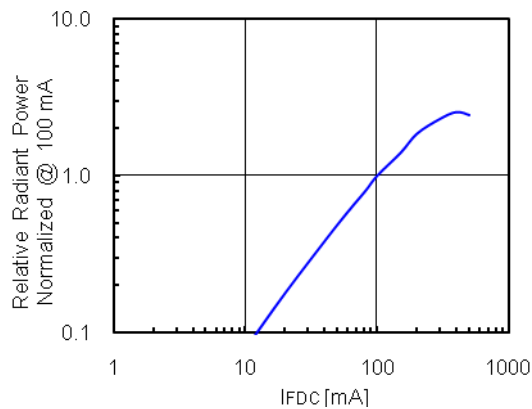
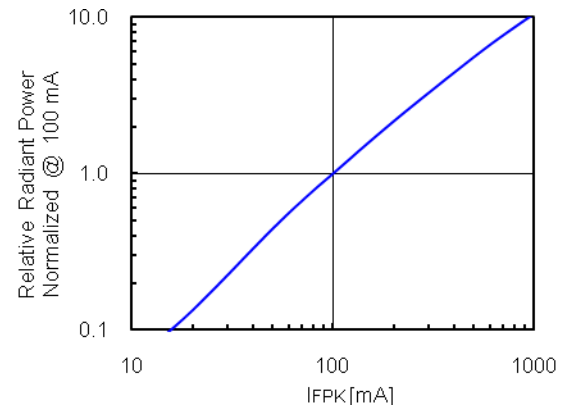
Fig 3. Relative Radiant Power
vs. Forward DC CurrentFig 4. Relative Radiant Power
vs. Forward Peak Current

Fig 5. Forward DC Voltage vs. Temperature

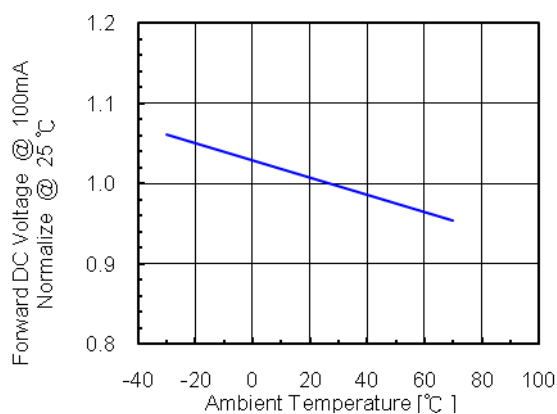


Fig 6. Relative Radiant Power vs. Temperature

